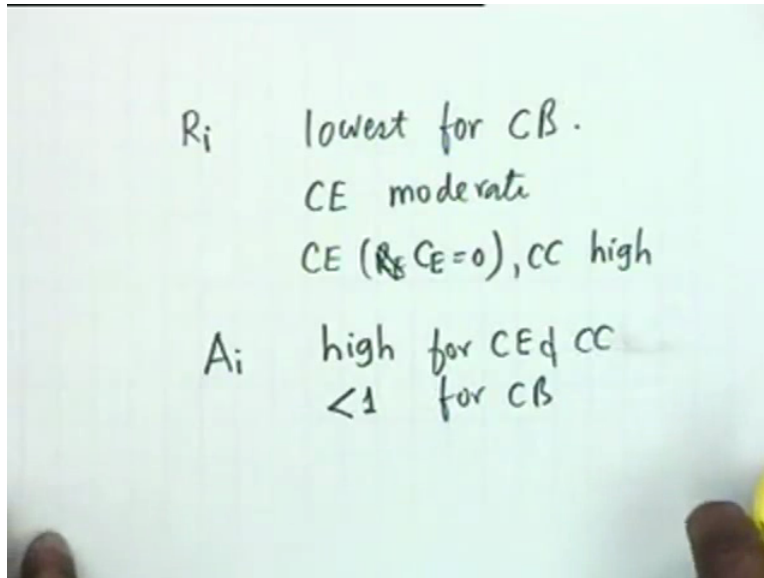


Analog Electronic Circuits
Professor S. C. Dutta Roy
Department of Electrical Engineering
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Lecture no 14
Module no 01
Midband analysis of FET Amplifiers

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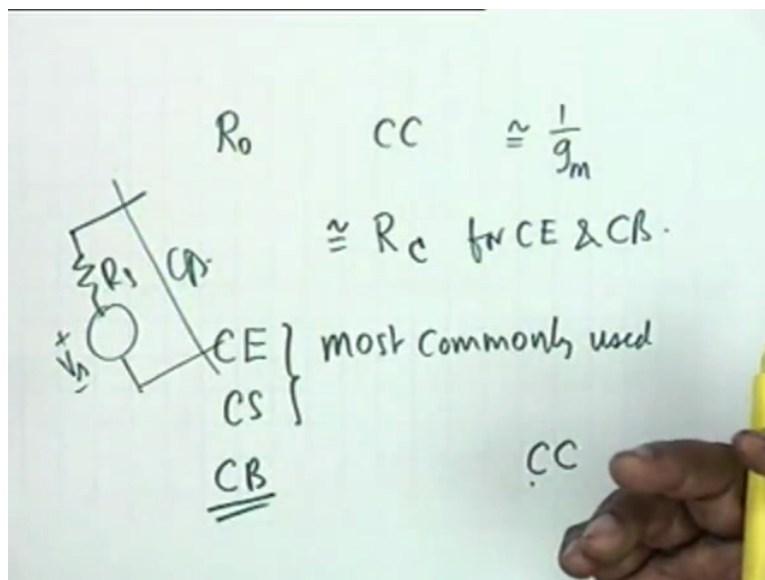
14th lecture and we are going to do midband analysis of FET amplifiers. So far we are concerned with BJT and BJT we discussed the CE connection, the CB connection common base and the CC connection common collector or the emitter follower. And you shall see that FET amplifiers are very similar in analysis and performance characteristics, for example, CE is comparable to common source CS, emitter terminal is comparable to the source terminal, common base is comparable to CG common gate, and common collector is comparable to common drain. Now what are these characteristics?

If I take voltage gain A_v then is the same for CE and CB that is g_m minus... No, there is a difference there is difference of phase, in CE there is an inversion, in CB there is no inversion but the again magnitude is the same g_m times R_L parallel R_C okay. However, if CE is unbypassed R_E then the gain drops down drastically agreed, unbypassed emitter resistance the gain drops down drastically. Whereas for CC, A_v the voltage gain is less than 1 but very close to

unity very close to unity. These characteristics as you shall see will be the same if E is substituted by S, D is substituted by G in the case of the FET amplifier.

As far as the input resistance is concerned, the lowest input resistance is for which connection, C B common base connection is the lowest, for CE it is moderate and CE with R E unbypassed how do I indicate this, let us put $C E = 0$ that indicates that R E is unbypassed and CC input resistance is very high, it is of the order of $r_{Pi} + \beta + 1$ times R E. The current gain current gain is high for CE and CC but it is less than 1 for common base CB.

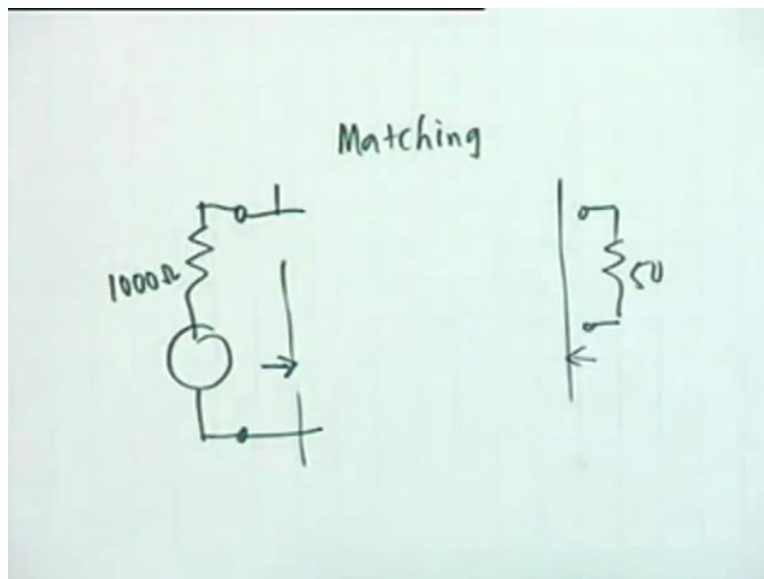
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As far as R_o is concerned which configuration has the lowest R_o ? Common collector, and R_o is of the order of 1 over g_m , or the other 2 configurations they are approximately $= R_{sub C}$ for CE and CB, and whatever we have said so far about common emitter also applies to common source, common base also applies to common gate and common collector also applies to common gate. Of the 3 configurations the most generally used configuration is the common emitter, common emitter is the general-purpose configuration because it has moderate voltage gain, moderate current gain, its input impedance is neither very large nor very low, output impedance is of the order of $R_{sub C}$ so it is at your choice, this is the most commonly used. In FET it would be the common source okay, most commonly used.

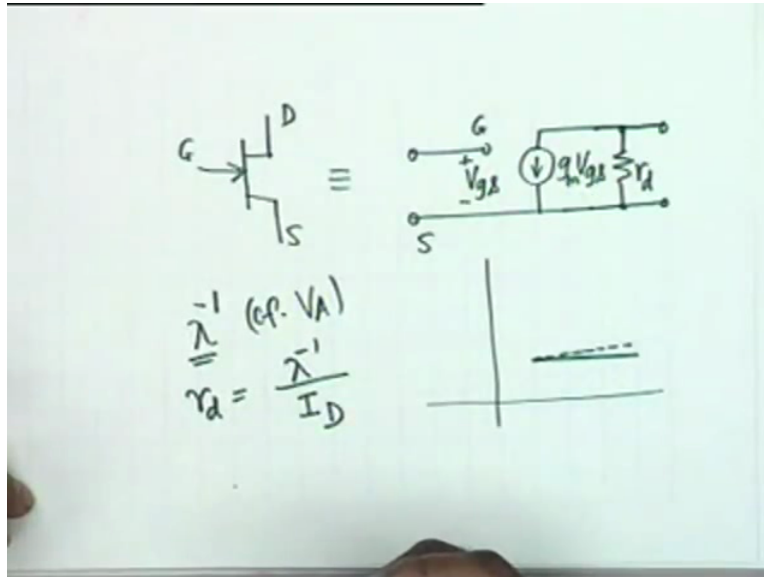
Now there are 2 special uses of the common base, one special use for common base, one special use for common collector, what is this for common base? If you are driving if your signal source is high impedance then you apply to the common base because the input impedance is low. On the other hand, if your signal source has high impedance $V_s R_s$ okay then you apply to a common base so that it is a current I basically, a source having high impedance is a current source okay more than a voltage source so it is at the apply a common base circuit, where as a common collector circuit is used where the source is a voltage source that means input impedance is low okay. And the common collector circuit the other use is that it acts as a buffer from a high impedance source to a low impedance load okay.

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In the in the tutorial class this week there is a problem of there is a problem that is given for matching a source to a load alright. The source impedance is 1000 ohms and the load impedance is 50 ohms, obviously if we connect directly if we connect the source to the load directly there may be mismatch, so if you want to deliver maximum power to the load then what you do is, you insert an amplifier in between such that the input impedance is 1000 ohms and the output impedance is 50 ohms okay, so this is the problem of matching and an amplifier can very well fit the purpose, the problem you shall do yourself.

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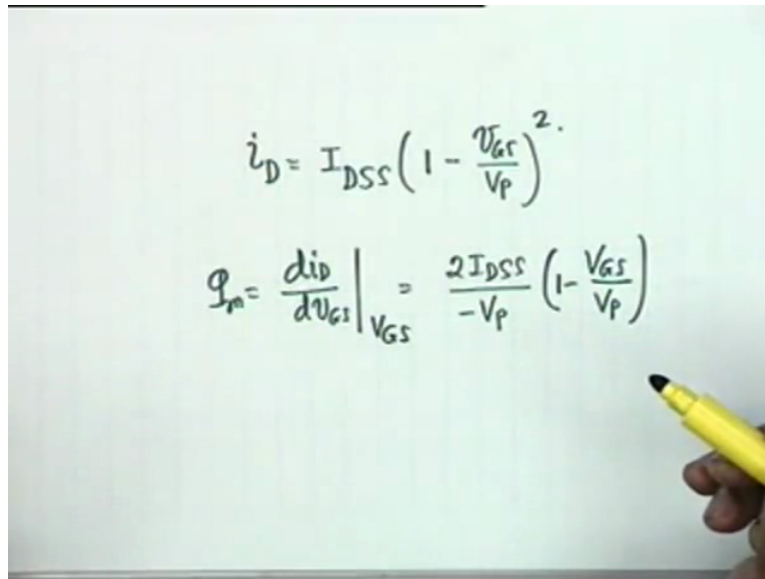


$$\frac{-1}{\lambda} \text{ (cf. } V_A) \\ r_d = \frac{\lambda^{-1}}{I_D}$$

Now let us take an FET amplifier, the basic equivalent circuit basic equivalent circuit that we shall use for an FET, this is the gate, this is the drain, this is the source, basic equivalent circuit would be the gate is open, this is the source this voltage is V_{gs} the phasor voltage and then you have a current generator g_m times V_{gs} g_m times V_{gs} and it is parallel by a dynamic drain resistance $r_{sub d}$ which occurs due to non-parallel nature of the characteristics with respect to the voltage axis. If you draw the FET characteristics, these are not perfectly parallel but they are slightly inclined and this slight inclination and the BJT this was called early effect, in the FET there is no special name for it but there is a voltage comparable to the early voltage and for reasons to be made clear in another course this is denoted by λ inverse okay.

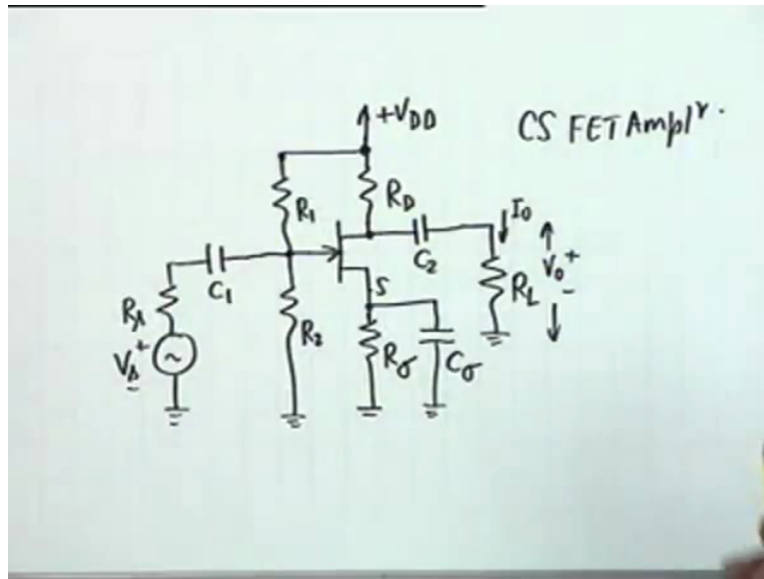
λ inverse is comparable $C_F V_{sub a}$, the early voltage in BJT, it is for peculiarisms it is called λ inverse okay. And $r_{sub d}$ you can find from the characteristics, you find its slope okay that is you extend this on the negative axis and find out where it cuts and that voltage divided by the current, you can do it that way or the λ inverse is given then $r_{sub d}$ is given by λ inverse divided by $i_{sub D}$ the drain current, in the previous case it was V_A divided by $I_{sub C}$ okay, it is very comparable very much comparable, r_d is the dynamic drain resistance.

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$$i_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_P}\right)^2$$
$$g_m = \left. \frac{di_D}{dV_{GS}} \right|_{V_{GS}} = \frac{2I_{DSS}}{-V_P} \left(1 - \frac{V_{GS}}{V_P}\right)$$

As far as g_m is concerned, g_m can no longer be calculated by a simple formula like the one that you had used that is I_{DSS} divided by 26 no, no longer that because your drain current i_D is not a linear relationship, it is a relationship like this it is a square $1 - V_{GS}$ divided by V_P whole square where V_P will be replaced by V_T if it is an enhancement mode MOSFET. And g_m has to be found out as di_D/dV_{GS} at the operating point at the operating point, and you can see that this is twice I_{DSS} divided by V_P times $1 - V_{GS}/V_P$, did you notice that I have changed the total voltage to the DC voltage because you shall have to find this g_m at the operating point and every time you shall have to find this therefore for the transistor that is specified you must be given V_P the pinch off voltage or V_T the threshold voltage, we shall see how these are calculated when you take an example.

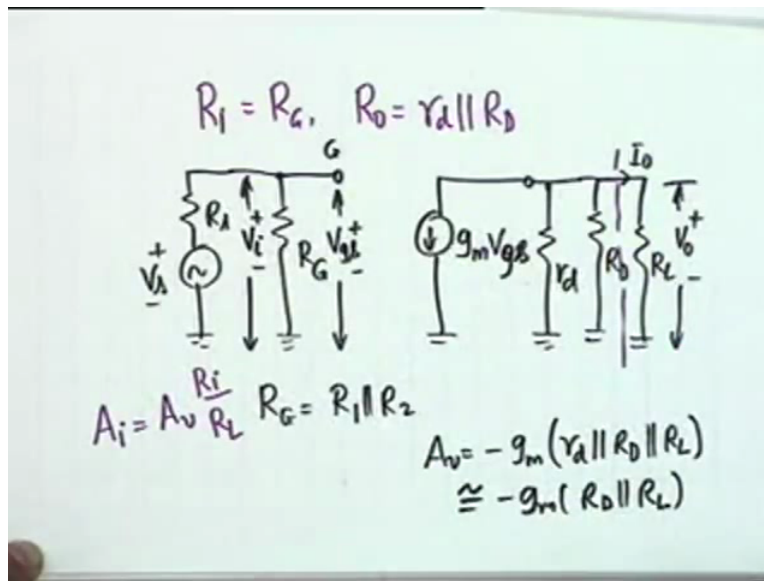
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Now the analysis is very routine and similar to what we had done for BJT so we will go a little hurriedly, not quite hurriedly we will miss we will meet some of the algebraic steps okay. I will simply say this is how the equation is written and you simplify and find out the result alright, but as far as you are concerned I suggest that you do it yourself very carefully. 1st of common source amplifier, you have a V_{DD} and usual story $R_{sub D}$ you have the... I am drawing the FET always as a JFET but it should be clear that the same circuit applies to MOSFET also, only the symbol shall differ okay, was simplicity I am drawing it like this okay.

This is the source and the source as you know is connected for biasing reason is connected to resistance R_{Sigma} and you know why $Sigma$ was used because R_s is reserved for source resistance alright. And as usual R_{Sigma} has to be bypassed by a C_{Sigma} alright, the output is taken from the drain through a coupling capacitor C_2 and you go to a load R_L , the voltage across R_L is the output voltage V_0 and the current in R_L is the output current I_0 . As far as the the what is the nature of the channel for the FET that I have drawn? N channel therefore, what I need is a biasing through R_1 and R_2 the usual story however, I want V_{gs} to be positive or negative? Negative, I want V_{gs} to be negative and therefore V_G must be less than V_s alright, we will see how this is done then you have the coupling capacitor C_1 and the source R_s and the source voltage V_s once again it is the phasor, this is the common source FET amplifier alright.

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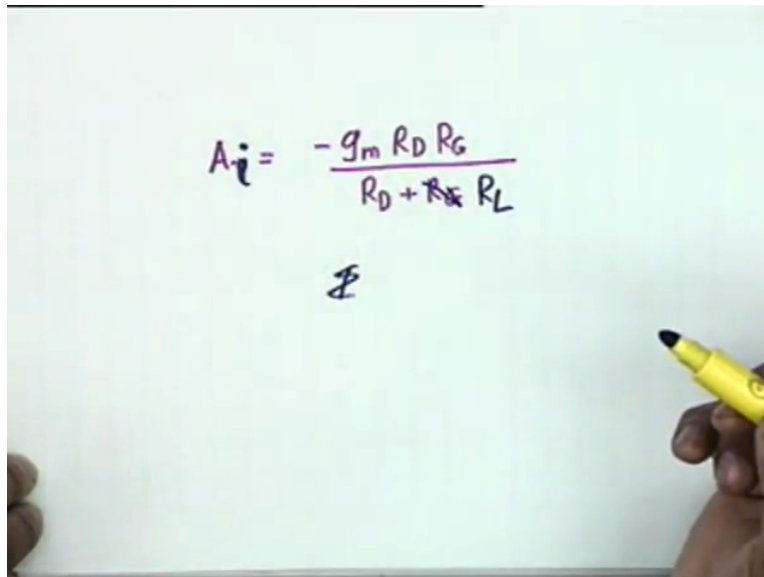


The equivalent circuit AC equivalent circuit can be drawn is the best that, we start with R_s, V_s, C_1 is a short, R_1 and R_2 in parallel shall give you a resistance of recall this $R_G, R_G = R_1$ parallel R_2 okay. And the gate is now open alright, the gate is now open, the source is shorted to ground as far as AC is concerned the source is shorted to ground so the only other terminal that we need is the drain and the drain has a current generator $g_m V_{gs}$ is this voltage which is also = be V_i in our usual terminology, the actual voltage that is applied to the gate between the gate and ground okay, so $V_i = V_{gs}$ $g_m V_{gs}$, then we have the drain dynamic drain resistance r_{sd} and the 2 resistances capital R_D and capital R_L , it is this voltage which is the output voltage and the current through R_L is the output current I_0 .

It is very easy to see that the gain because V_{gs} is the same as V_i, V_o by V_i shall be simply $-g_m$ because this current does not agree with voltage, times r_d parallel R_D parallel R_L that is it very simple the voltage gain, and usually small r_d is a very large quantity therefore the gain in approximately $-g_m R_D$ parallel R_L , if you so desire you can denote this resistance by R_L prime as we did in the BJT. Also, you looking at the circuit itself you can see that the input resistance R_i is simply = R_G , no complications no r_{pi} , no r_x no further feedback so $R_i = R_G$ and what about R_o ? If you look from here it is simply the parallel combination of r_d parallel R_D because the current generator is a 0 current generator and it has internal impedance of infinity.

0 because V_s is 0 then V_i shall be = 0 alright, and therefore we have found out the gain and the 2 impedances by inspection, the only thing that remains to find out is A_i which is a current gain is given by A_v times R_i by R_L and it is very easy to see what this expression would be.

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$$A_i = \frac{-g_m R_D R_G}{R_D + R_G + R_L}$$

“Professor–student conversation starts”

Professor: This would be =, A_v would be = $-g_m R_D R_G$ divided by $R_D + R_G$ is that correct?

Student: R_L .

Professor: R_L that is correct, this should be R_L .

Student: In the numerator also.

Professor: No, in the numerator R_L cancels out.

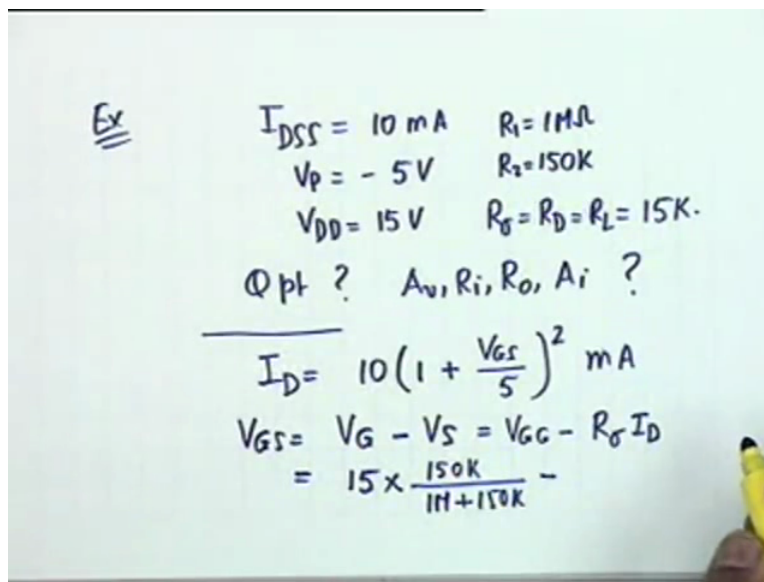
Student: This is A_i sir.

Professor: Oh this is A_i this is A_i , now it is correct? Fine we will take an example. See analyses is very simple, it is much simpler than BJT why, because the gate is isolated from the source and the drain okay, gate does not have the forward feedback path so the analysis is very simple and it can be done by inspection

“Professor–student conversation ends”

Let us take an example, we have a common source FET amplifier please look at this carefully, I_{DSS} , the calculation is a little complicated more involved than BJT because of the trouble of finding g_m okay, and because V_{GS} is $V_G - V_S$, you have to make sure that V_{GS} is negative, you have to make sure that V_{DS} is greater than $V_{GS} - V_P$ alright, so you have to make all these things clear otherwise the transistor will not work as an amplifier, all these checks were not needed. As long as Q point is found out in a BJT, a Q point which is reasonably a good Q point you have to worry about nothing else, in an FET you do have to, let us see.

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Ex

$$I_{DSS} = 10 \text{ mA} \quad R_1 = 1 \text{ M}\Omega$$
$$V_P = -5 \text{ V} \quad R_2 = 150 \text{ K}$$
$$V_{DD} = 15 \text{ V} \quad R_\sigma = R_D = R_L = 15 \text{ K}$$

Q pt ? A_v, R_i, R_o, A_i ?

$$I_D = 10 \left(1 + \frac{V_{GS}}{5} \right)^2 \text{ mA}$$
$$V_{GS} = V_G - V_S = V_{GG} - R_\sigma I_D$$
$$= 15 \times \frac{150 \text{ K}}{1 \text{ M} + 150 \text{ K}} -$$

I_{DSS} is 10 milliamperes given, V_P is given as - 5 volt, V_{DD} is 15 volt, R_1 is 1 Megohm, R_2 is 150 K and $R_\sigma = R_D = R_L$, all these 3 resistors are equal and value is 15 K alright. The question is to find the Q point and also the values of A_v, R_i, R_o , and A_i , these are the things to be found out in common source amplifier. Now the 1st thing you do is to find out the drain current the Q point drain current and you know the drain current $I_{sub D}$ is I_{DSS} that is 10 milliamperes, $1 - V_{GS}$ divided by V_P so that is $1 + V_{GS}$ divided by 5 whole square milliamperes is that clear, because V_P is - 5 so the sign has become positive okay.

Also you see $V_{GS} = V_G - V_S$, what is V_G ? V_G is V_{GG} V_G is $V_{GG} - R_\sigma I_D$ therefore V_{GS} what is V_{GG} , this is 15 multiplied by R_2 that is 150 K divided by 1 megohm +

150K – R Sigma is 15 K time I D. Substitute this here, then you get an equation in I D which is not a linear equation which is not a linear equation which is quadratic.

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$$\begin{aligned}I_D &= 0.4 \text{ mA} \\V_{GS} &= 1.96 - 15\text{K} \times 0.4 \text{ mA} \\&= V_{GG} \\&= V_G \\&= -4.04 \text{ V} \\V_{DS} &= 15 - 0.4 \text{ mA} (30\text{K}) \\&= 3 \text{ V}\end{aligned}$$

And the equation after you clear the algebra and solve it okay, I will skip all this arithmetic you get $I_{sub D} = 0.4$ milliamperes. Now a quadratic has 2 solutions, you must be careful in choosing the solution, the other solution will make the FET not operate in the linear region alright, the other solution would not be acceptable therefore V_{GS} if I_D is 0.4 milliamperes, you will get V_{GS} as $1.96 - 15\text{K}$ this is V_{GG} Incidentally, which is also $= V_G$ 15K multiplied by 0.4 milliamperes, this 6 volts and therefore V_{GS} is -4.04 volts. And under this condition V_{DS} is his V_{DD} that is $15 - 0.4$ milliamperes multiplied by $R_D + R_{Sigma}$ that means 30K alright $15 + 15$ and this comes out as 3 volts, 3 volts and 0.4 milliamperes is the Q point. Finally you have to check whether this V_{DS} is greater than $V_{GS} - V_P$, obviously it is so okay alright that you check yourself.

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$$g_m = \frac{2I_{DSS}}{-V_P} \left(1 - \frac{V_{GS}}{V_P}\right) \quad \cancel{\lambda}$$
$$r_d = 100 \text{ K} \quad \swarrow = 0.8 \text{ m}\Omega$$
$$A_v = -0.8 \text{ m}\Omega (100 \text{ K} \parallel 15 \text{ K} \parallel 15 \text{ K})$$
$$= -5.6$$
$$R_i = 1 \text{ M}\Omega \parallel 150 \text{ K} = 130 \text{ K}$$
$$R_o = 100 \text{ K} \parallel 15 \text{ K} = 13 \text{ K}$$

Now other thing that you needs to be found out is g_m and r_d , it is given that λ inverse for this no... r_d is given I will take the λ inverse case later, r_d is given as 100 K, how do you find g_m ? g_m is twice I_{DSS} divided by $-V_P$ then $1 - V_{GS}$ upon V_P , everything is known you can substitute the values and get g_m as = 0.8 millimho be careful in this calculation. And then once you have found this out, the other things are simply putting down the formula or just looking at the circuit, you can write down the equation by looking at the circuit. A_v would be $-g_m$ that is 0.8 millimho parallel combination of 100 K, 15 K and 15 K, R_D , R_L , r_d this comes out as - 5.6.

$R_{sub i}$ which is R_G is 1 megohm parallel 150 K and this comes as 130 K. R_o would be if you take small r_d into account, 100 K parallel 15 K and this becomes 13 K alright, now let us complicate matters, is there any question on this? If I can proceed at this rate we will be in good business.

“Professor–student conversation starts”

Student: Excuse me sir.

Professor: Yes.

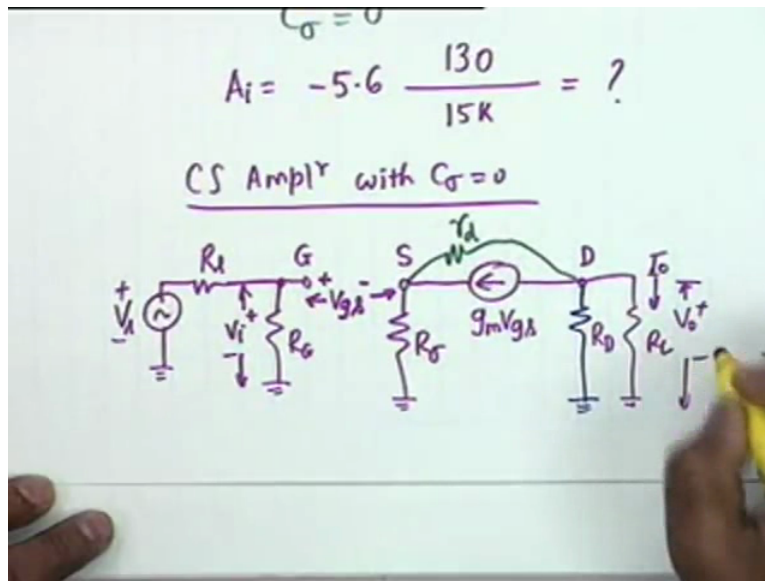
Student: When you have a resistance R_E , will not that change the equation for I_D (())(26:18)

Professor: Small r_d ?

Student: Yes.

Professor: Small r_d comes only in the AC equivalent circuit, not in the DC. Small r_d comes only in the AC equivalent circuit (26:36).

(Refer Slide Time: 26:43)



We next consider next complicate matter, let us put $C_\sigma = 0$ that is an unbypassed source resistance, now what will be the... Yes.

Student: Sir we have not found the current gain.

Professor: We have not found the current gain oh, $A_{sub i}$ is A_v that is - 5.6 multiplied by R_i , R_i is 130 K divided by R_L is 15 K, you calculate what this value is okay.

“Professor–student conversation ends”

Okay so let us consider a CS amplifier, $C_\sigma = 0$ and all that we have to do now is to draw the equivalent circuit carefully and that solves the problem as you shall see. The equivalent circuit if we proceed in the usual manner, V_s , R_s then you shall have R_G the same circuit this is the gate, then since the source is not bypassed we must include R_S agreed, and this is the voltage which is $V_{gs} + -$. No longer it is to ground no longer $V_{gs} = V_i$, no V_{gs} is not = V_i

agreed, oh one thing that I did not calculate was A_v which you can very easily find out as A_v multiplied by R_i divided by $R_i + R_i$ that is very simple so I do not have to repeat that, let me go to only procedures which are new.

Then from the drain to the source we have $g_m V_{gs}$ and to complicate matters there is an r_d , we will see what happens when r_d is included what happens when r_d is not included, and I find it convenient to leave all complicated matters to students so including the effect of r_d I will ask you to calculate yourself, we will have occasion to look at this. And in this particular case in this particular example that we took, r_d cannot be ignored and we shall see in a moment, that we shall do it we will make a rough calculation. From the drain then we have 2 resistances R_D and R_L , this is I_0 and this voltage is V_0 alright. Now you see look at the circuit it is said that if you can observe a problem carefully, half of it is solved.

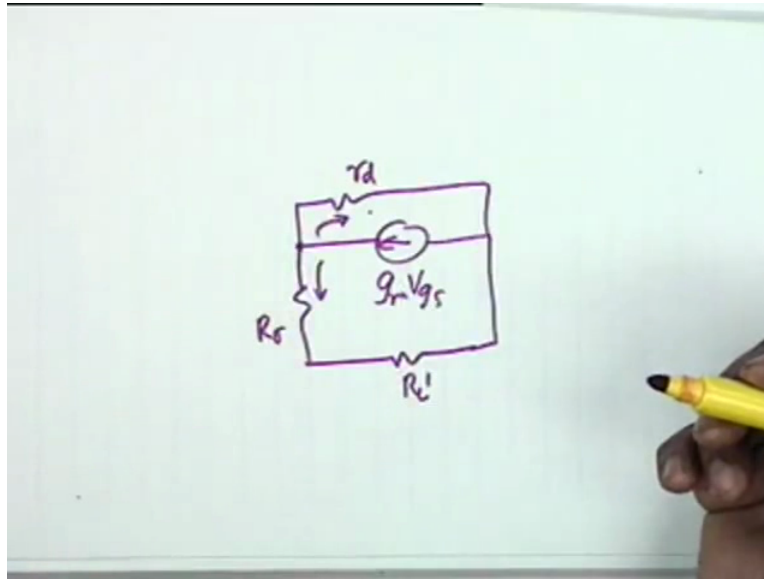
If you observe this circuit carefully the calculations will be very simple, $g_m V_{gs}$ now no longer supplies only the parallel combination of R_D and R_L and small r_d , small r_d is not in parallel at all so this current source must supply 2 parallel paths; one is r_d and the other is the parallel combination of R_D R_L and in series with R_{Sigma} okay, if you recognise this fact then the calculation including the effect of r_d shall be simple but we will find it convenient to ignore it.

Student: Sir (30:43)

It supplies... You see across $g_m V_{gs}$ there are 2 resistors; one is r_d and the other is R_D parallel $R_L + R_{\text{Sigma}}$ okay because these points are the same these points are the same they are all ground, so what I have is R_D parallel $R_L + R_{\text{Sigma}}$. If you recognise this is the only single fact that has to be recognised to include the effect of r_d . Now can we ignore the effect of r_d in this case? r_d was given to be 100 K, the parallel combination of R_D and R_L is 7.5 K and this is 15 so the parallel part is 22.5 K approximately one fifth of this part because the current shall be varying into the same ratio 1 is to 5 is that clear?

Student: Yes, how does $g_m V_{gs}$ provides current to r_d ?

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Oh there is a current source let me draw this, $g_m V_{gs}$ which is in parallel with small r_d okay, this point then we have $R_{\sigma} + R_{L'}$ therefore this current has 2 paths; one is through this and the other is through this, is not that right this current after coming here where can it go, it has to flow like this and like this. Now if this part was very low resistant as compared to small r_d you could have ignored small r_d , but the current now divides into approximately 1 is to 5 alright so we cannot ignore r_d but we will make our calculation excluding r_d and leave r_d effect to you.

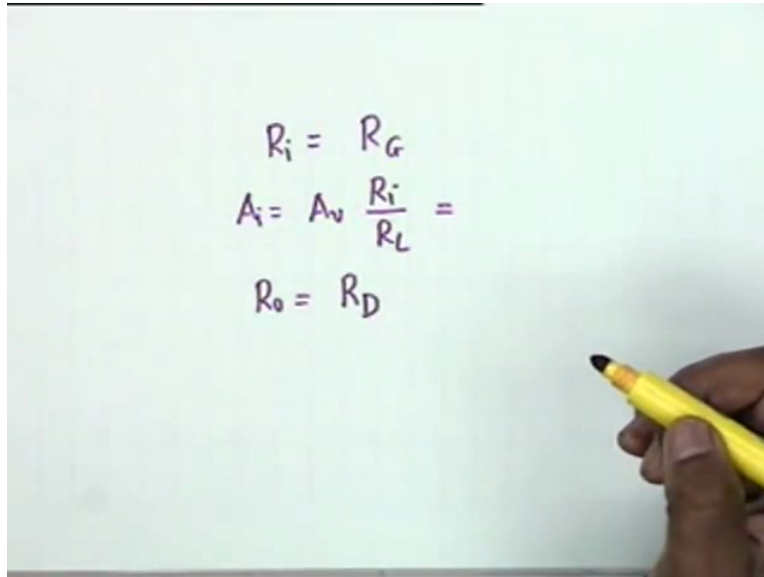
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$$r_d \gg R_\sigma + R_D \parallel R_L.$$
$$V_{gs} = V_g - V_s = V_i - g_m V_{gs} R_\sigma$$
$$V_{gs} = \frac{V_i}{1 + g_m R_\sigma}$$
$$V_o = -g_m V_{gs} (R_D \parallel R_L)$$
$$A_v = \frac{-g_m (R_D \parallel R_L)}{1 + g_m R_\sigma}$$

So we assume that r_d is much greater than $R_\sigma + R_D \parallel R_L$ okay, we assume we have derived our formula by assuming this. If that is so then you see then you see that V_o is simply $-g_m V_{gs}$ multiplied by $R_D \parallel R_L$ so on that 1st thing found out is V_{gs} , let us see what V_{gs} is. V_{gs} is $V_g - V_s$ that = V_g is V_i right V_g is V_i and V_s is if we ignore small r_d then $g_m V_{gs}$ flows through R_σ therefore it would be simply $g_m V_{gs}$ multiplied by R_σ okay, this is an involved equation V_{gs} occurs in the right side and also in the left side so you can find out V_{gs} as = V_i divided by $1 + g_m R_\sigma$ agreed, this is how V_{gs} has to be found out. And once V_{gs} is found out, V_o is $-g_m V_{gs} R_D \parallel R_L$ and therefore the voltage $A_{sub v}$ shall be = $-g_m R_D \parallel R_L$ divided by $1 + g_m R_\sigma$.

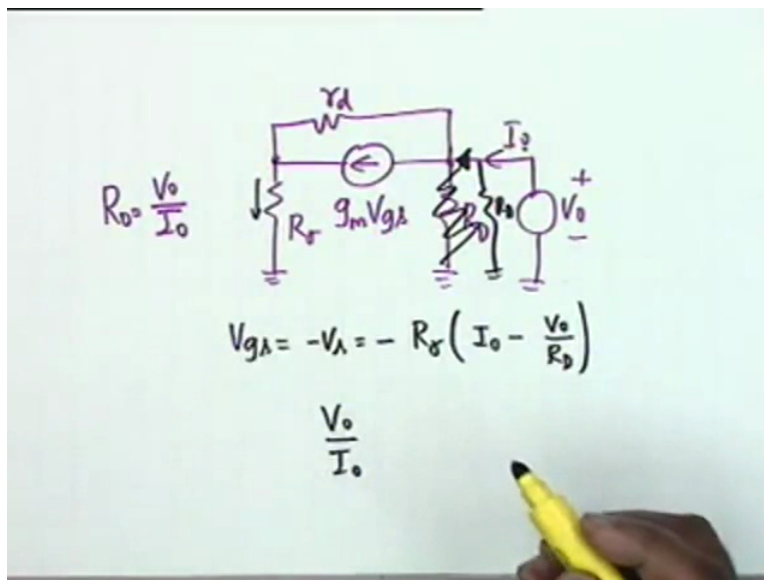
What was g_m in the previous example? 0.8 millimho and R_σ was 15 K so this is 12, is that right? 12 is much larger compared to 1 by approximately the gain would be, if $g_m R_\sigma$ is much greater than 1 then approximately the gain would be $-R_D \parallel R_L$ divided by R_σ . You recall we had a similar formula in the case of a common emitter amplifier with unbypassed R_E , the inverse approximately negative of the ratio of the effective load to R_E , it is the same formula that applies here okay.

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What is R_i ? Input resistance, it = $R_{sub G}$ agreed and $A_{sub i}$ can be calculated as $A_v R_i$ divided by R_L in the usual manner you can write the expression. What is R_o ? If small r_d is ignored then R_o is simply R_D but if it is not ignored then complications arise and you have to solve a circuit, let me indicate the circuit the solution would be left to you.

(Refer Slide Time: 36:03)



What you have to do is we have an R_{Sigma} then $g_m V_{gs}$ okay $g_m V_{gs}$ alright parallel r_d and there is a resistance $R_{sub D}$, you have to correct a voltage generator here and the current I

0 has to be found out. R_0 would not be $= V_0$ by I_0 alright, but what is V_{gs} ? $-V_s$ okay. And what is $-V_s$? This is minus, what is the current flowing through this?

Student: V_0 by R_{σ} .

Professor: No.

Student: V_0 by $R_D + R_{\sigma}$.

Professor: It is R_{σ} multiplied by what is the current that is what we want to know... In terms of I_0 V_0 , if it is $I_0 - V_0$ by R_D alright so you know everything now in terms of I_0 and V_0 and that way you can find out V_0 by I_0 , is the point clear? No, alright let me draw this resistance here R_D then this current must flow through the R_{σ} , this current after this current is $I_0 - V_0$ by R_D this current this current this one. This current splits up in the 2 parts; one is through this, one is through this, they must combine here and flow through R_{σ} it was a little bit of thinking but it is not difficult so you can find out V_0 by I_0 and I leave this to you.

“Professor–student conversation starts”

Student: Sir but out of this V_0 by I_0 will also go into small r_d .

Professor: Whatever it is whatever this current is, these 2 currents again combine here and flow through R_{σ} okay, any questions?

Student: Sir what happens to $g_m V_{gs}$?

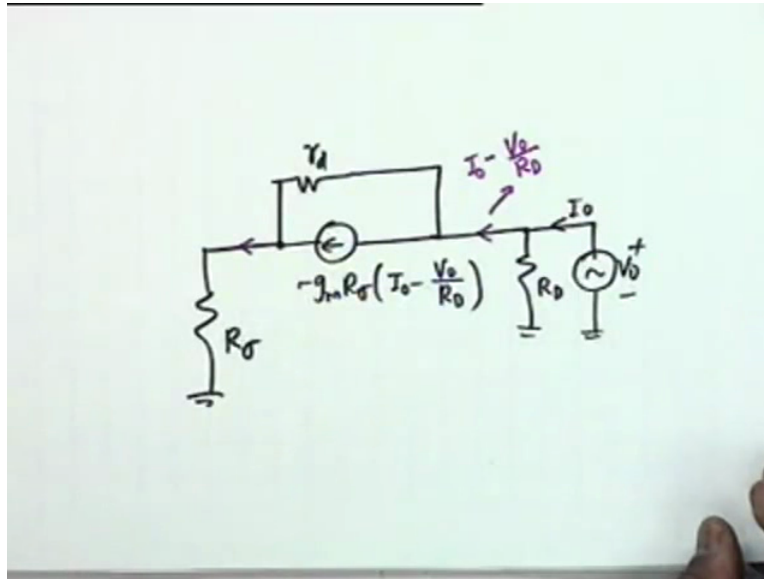
Professor: Oh this is what we have found out, $g_m V_{gs}$ will be $-g_m R_{\sigma}$ times $I_0 - V_0$ by R_D , everything now in the circuit shall be in terms of I_0 and V_0 , which current source?

Student: Sir is it not contributing current to R_{σ} .

Professor: Let me draw this circuit again, now I shall try in a different manner.

“Professor–student conversation ends”

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This will be $-g_m R_S (I_D - \frac{V_o}{R_D})$, there is an R_D here, this is V_o , I_D and this goes to R_S alright. So whatever current comes here whatever current comes here must flow here, there is no other way. And what is this current? This is simply $I_D - \frac{V_o}{R_D}$ this is what I have substituted for V_{gs} , V_{gs} is $-R_S$ multiplied by this current okay, any other doubt? I assume this is correct, I have not made any mistake yes oh sure I have all the time in the world, you must give me a signal when you are through. We shall then consider the same example that we have considered for the CS amplifier with C_S tends to what? The previous example tends to infinity that is R_S short-circuited.

Student: Sir can we have the formula for R_o ?

Professor: No I have not derived it therefore you have to derive it yourself.

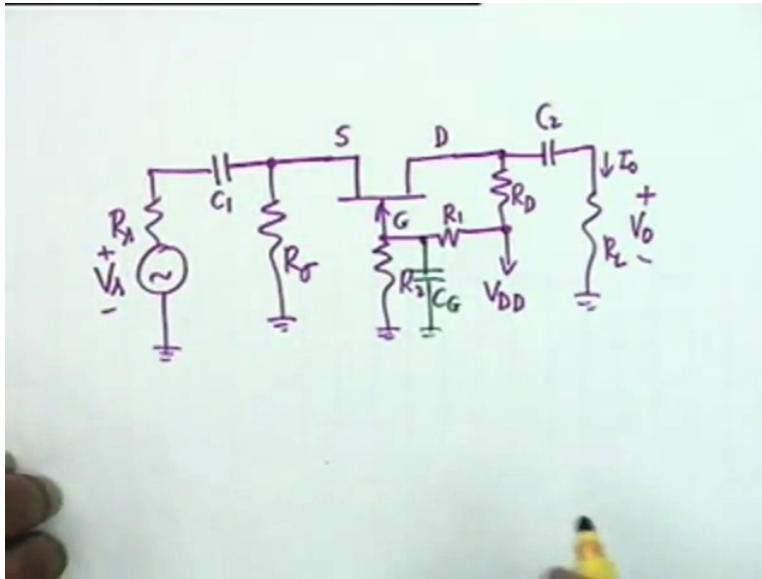
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Ex $I_{DSS} = 10 \text{ mA}$, $V_P = -5 \text{ V}$, $V_{DD} = 15 \text{ V}$,
 $R_1 = 1 \text{ M}$, $R_2 = 150 \text{ K}$,
 $R_G = R_D = R_L = 15 \text{ K}$
 $g_m = 0.8 \text{ mS}$; $r_d = 100 \text{ K}$
 $A_v = -0.46$
 $A_i = -4$
 $R_i \neq R_o$ same.

Consider the same example, what was the example? I_{DSS} 10 milliamperes, V_P is - 5 volts, V_{DD} is 15 volts, R_1 is 1 megohm, R_2 150 K, $R_{\text{Sigma}} = R_D = R_L = 15 \text{ K}$. Small r_d if it is 100 K then obviously all our calculation will be approximate okay. Nevertheless I give you small r_d and I ask you what to find what modification is needed, we have already seen the modification, in the calculation output resistance all that you have to do is to split this current $g_m V_{gs}$ that is about it okay so it should not be very difficult, small r_d is 100K. If you calculate will the Q point change? No, because everything has remained the same, Q point does not change. If Q point does not change, g_m does not change g_m is the same g_m is also same as 0.8 millimho

And if you utilise these formulas then you get A_v do not depend on formulas unnecessarily, where you can see the formulas see it rather than committing to memory okay. If you if you calculate it is simply $-g_m$ the effective load divided by, this divided by comes because $C_{\text{Sigma}} = 0$, divided by $1 + g_m R_{\text{Sigma}}$ and that becomes - 0.46 I will skip the arithmetic, $A_{\text{sub } i}$ becomes - 4 now you see A_v the voltage gain now becomes less than 1 this is what the unbypassed emitter source resistance does to the amplifier. The current gain is - 4, R_i and R_o are not changed they are the same as in the previous case okay done, let us take the common gate amplifier. You will see that the calculation is very similar there is no difference except that we have to be bit careful about the calculation of g_m and the output resistance, it is the output resistance which is the complicated calculation.

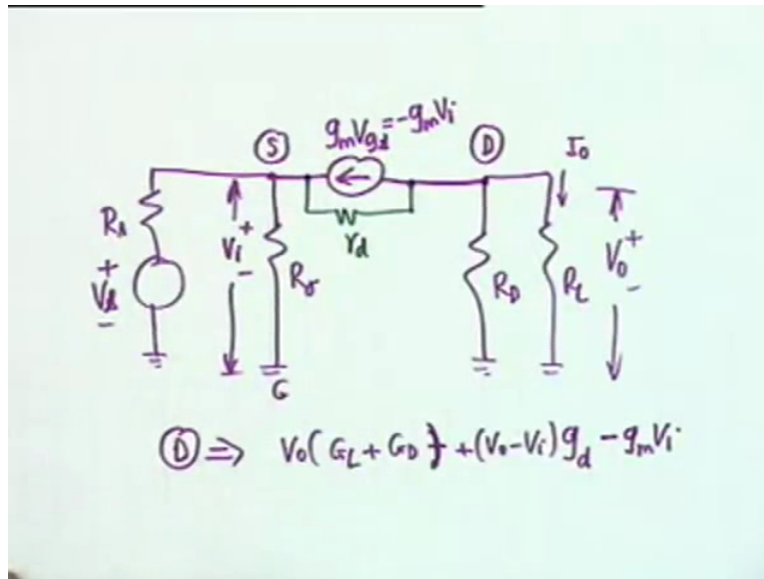
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Now in a common gate amplifier CG which is equivalent to CB of BJT, you have V_s , R_s , capacitor C_1 started on a wrong foot so let us change the page. We have first let us draw the FET, this is the source this is the gate and this is the drain. Now in order to bias those in order to bias the source we require a resistance R_σ and we cannot bypass it now, we cannot bypass it. In order to put a gate voltage we must have a resistance R_2 and we must supply it to the V_{DD} okay, from the drain we have the resistance R_D this is R_1 and should go to $+V_{DD}$. From here you take the coupling capacitor and take the load R_L , the voltage is V_o the current is I_o and for reasons that I had stated in the case of common base amplifier R_2 must be bypass.

In other words there must be a capacitor here C_G okay there must be a capacitor here which bypasses R_2 to ground but R_2 is effective in DC inserting the DC operating point. Then your input is applied through a coupling capacitor and a source resistance R_s and a voltage source V_s and this goes to ground alright. Now things will get little complicated because of r_d why? It can be very easily ignored in a BJT, you have to be very in FET. As I said in the last analysis in the last example that we took our figures were very rough because small r_d was not negligible compared to the parallel combination of $R_D R_L$ and in series with R_σ okay that makes me happy, now let us see what is the equivalent circuit is.


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We have R s, V s AC equivalent circuit, then you have the source node from which you have an R Sigma and this voltage is V i okay, and this comes to from the drain to the source the gate is common gate is grounded, from the drain to the source you have g m V gs, what is V gs =? - V i, is that clear? This is the gate G so V gs is from this point to this point which is of opposite polarity to V i but magnitude is the same so I could write this in - g m V i this is a simplification occurring immediately. And then you have this (())(47:29) of r sub d the dynamic drain resistance. And from here you have the R D and R L and this is V 0 and this is I 0 okay, the things are not too bad as far as the equivalent circuit is concerned because there are only 2 nodes.

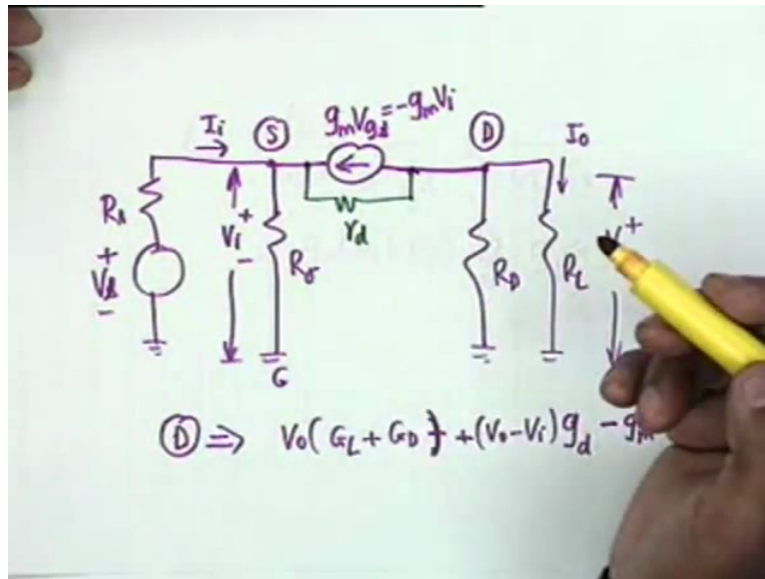
Not only that since we are finding out the gain, again is a relationship between V 0 and V i, you can write the node equation at D in terms of V i and V 0 nothing else. As you can see node equation of D is V 0 G L now I take conductance, it becomes simpler to do it that way, G L + G D +... then V 0 - V i divided by R D so + V 0 - V i multiplied by g d okay is that current through r d. Then I have this extra term - g m V i okay this is the node equation and the node equation contains only V 0 and V i why this? I have to add this current, this current and this current and this current, this current is g m V gs which is - g m V i okay.

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$$A_v = \frac{g_d + g_m}{G_L + G_D + g_d} \cong \frac{g_m}{G_L + G_D}$$
$$= g_m (R_L \parallel R_D) \quad \text{if } \frac{g_d}{G_L + G_D} \ll 1$$


So since this equation contains only V_0 and V_i , it is very easy to find out the voltage gain and the expression is $g_d + g_m$ divided by $G_L + G_D + g_{\text{subscript } d}$ and if r_d could be ignored if it could be ignored, wishful thinking it will should have been approximately g_m divided by $G_L + G_D$, do not you see that this is same as $g_m R_L \parallel R_D$, is this obvious? 1 by $G_L + G_D$ conductance is add so the 2 resistors are in parallel. This is also obvious for the equivalent circuit okay equivalent circuit never tells a lie, if r_d is ignored if it is infinity then this current has to flow through this and that is the voltage gain, it is only because of r_d that we have to write a node equation at the node D otherwise we do not have to okay.

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If a big if g_d is much less compared to g_m as well as $G_L + G_D$ if this is true then this will be approximately the story. If you want to find out the input resistance, now the input resistance is also complicated by the occurrence of r_d okay and the occurrence of $-g_m V_i$ the input resistance is no longer R_{σ} okay. To find the input resistance all I need is the ratio of V_i to I_i okay, and therefore what I can do I can write node equation at the node s, if I write that at the node s, I_i is coming, $g_m V_{gs}$ is coming, $g_m V_{gs}$ is $-g_m V_i$, this current will be going of V_i by R_{σ} and current to r_d which is $V_o - V_i$ multiplied by G_D okay. Now the complication is that in this node equation you have V_o but you know what is V_o by V_i we have already calculated V_o by V_i and therefore it is not difficult.

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$$I_i = \frac{V_i}{R_\sigma} - g_m(-V_i) + \frac{V_i - V_o}{r_d}$$
$$\frac{1}{R_i} = \frac{1}{R_\sigma} + g_m + g_d - g_d A_v$$
$$\frac{1}{R_i} = G_\sigma + \frac{(G_L + G_D)(g_m + g_d)}{G_L + G_D + g_d}$$
$$\approx G_\sigma + g_m$$

The equation that we get is if you see it is V_i divided by R_σ is the current that is going – this current leaves, the current coming is $g_m V_i$ so this is $g_m - V_i$ is the current generator + $V_i - V_o$ is the current gain divided by r_d . Now what we do is we divide by V_i then you get $1/R_i$ as $= 1/R_\sigma + g_m$ then $+ g_d - g_d A_v$ that is right, now you substitute for A_v and simplify. The expression that I get it is a bit of algebraic simplification, not very complicated, you get $1/R_i$ as $= G_\sigma + G_L + G_D$, this requires a bit of algebraic simplification as I have said, $g_m + g_d$ divided by $G_L + G_D + g_d$ that is what I get. And once again if your wish comes true that if g_d is negligible compared to g_m and $G_L + G_D$, do not you see that it is simply $G_\sigma + g_m$ agreed.

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$$R_i \cong R_{\sigma} \parallel \frac{1}{g_m} \quad \frac{1}{.8} \text{ K}$$

\uparrow $\underline{1.25\text{K}}$

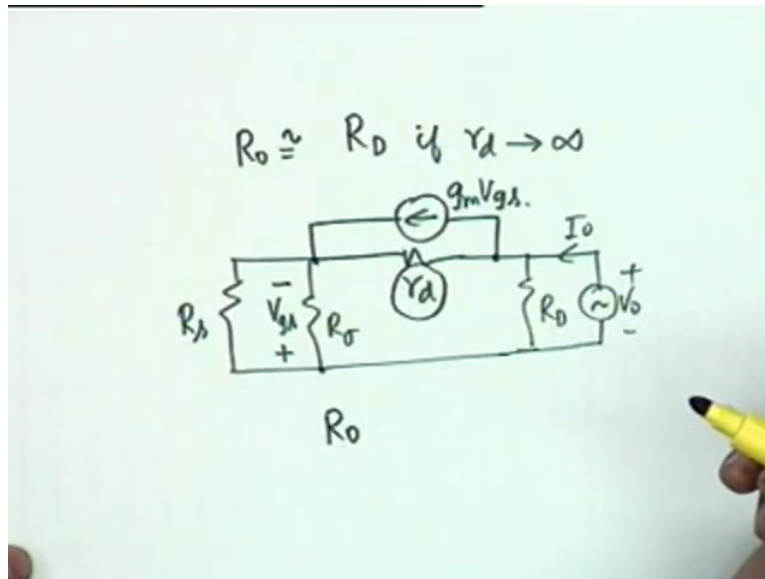
$$\cong \frac{1}{g_m}$$

$$A_i = A_v \frac{R_i}{R_L} \cong \frac{R_D}{R_D + R_L} < 1.$$

Which means that R_i is the parallel combination of R_{σ} and what else? $1/g_m$ okay, let us let us see this. R_i is approximately the parallel combination of R_{σ} and $1/g_m$, in the example that we took what was what was I am sorry I made a mistake because someone looked back, do not look back. R_{σ} parallel $1/g_m$ okay, what was R_{σ} in our example? 15 K, and $1/g_m$ is $1/0.8$ K which is 1.25, do not you see that R_{σ} is large compared to this and therefore this is approximately $1/g_m$. If you recall in the common base amplifier this was exactly the same story except that $1/g_m$ is now not as small as 25 ohms, in the previous case it was some 25-24 or 25 ohms, this is now 1.25K this is a generic story alright.

And finally of course A_i can be calculated from $A_v R_i$ divided by R_L we have found out the expression but I can mention that under this condition r_{σ} very large, this is approximately R_D divided by $R_D + R_L$ so the gain is current gain is less than 1, it has to be in a common base case this was also true. As far as R_o is concerned, the output resistance is approximately $= R_D$ if small r_d goes to infinity, if this is not the case then I am afraid you have to calculate this from this equivalent circuit.

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R_s , R_{Sigma} , r_d , $g_m V_{gs}$, where is V_{gs} now? V_{gs} occurs across R_{Sigma} and in what polarity? – up and + down agreed, so this is V_{gs} , this is $g_m V_{gs}$, it is not difficult to calculate, then you have an R_D and I_o and V_o , please do carry out these calculations okay and find out what is R_o , how does r_d effects of check on this calculation would be that if you put $r_d = \infty$ the value should be capital R_D that would be the check and this is a good point to stop, next time that is Thursday we will work out some problems and we will also look very briefly at the common what is remaining... Common drain Common drain FET amplifier.